

Product Description

Sirenza Microdevices' SBB-4089 is a high performance InGaP HBT MMIC amplifier utilizing a Darlington configuration with an active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 5V supply, the SBB-4089 does not require a dropping resistor as compared to typical Darlington amplifiers. The SBB-4089 product is designed for high linearity 5V gain block applications that require small size and minimal external components. It is internally matched to 50 ohms.

The matte tin finish on Sirenza's lead-free package utilizes a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding compounds that contain no antimony trioxide nor halogenated fire retardants.



Gain & Return Loss vs. Frequency (w/ BiasTees)

SBB-4089 SBB-4089Z



0.05-6 GHz, Cascadable Active Bias InGaP/GaAs HBT MMIC Amplifier



Product Features

- Available in Lead Free, RoHS compliant, & Green packaging
- IP3 = 35.2 dBm @ 1950MHz
- P1dB = 19.3 dBm @ 1950MHz
- Single Fixed 5V Supply
- Robust 1000V ESD, Class 1C
- Patented Thermal Design & Patent Pending Bias Circuit
- Low Thermal Resistance
- MSL 1 moisture rating

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- Wideband Instrumentation
- Wireless Data, Satellite Terminals

Symbol	Parameter	Units	Frequency	Min.	Тур.	Max.
S ₂₁	Small Signal Gain		850MHz 1950 MHz 2000 MHz	14.0 14.0 13.5	15.0 15.5 15.5	17.0 17.0 17.5
P _{1dB}	Output Power at 1dB Compression	dBm	850MHz 1950 MHz	18	19.0 19.5	
OIP ₃	Output Third Order Intercept Point	dBm	850MHz 1950 MHz	33.0	39.0 35.0	
Bandwidth	S ₁₁ , S ₂₂ : Minimum 10dB Return Loss (typ.)	MHz			4500	
S ₁₁	Input Return Loss	dB	1950 MHz	10.0	17.5	
S ₂₂	Output Return Loss	dB	1950 MHz	10.0	17.5	
S ₁₂	Reverse Isolation	dB	1950 MHz		18.5	
NF	Noise Figure	dB	1950 MHz		4.5	5.5
V _D	Device Operating Voltage	V			5	5.25
I _D	Device Operating Current	mA		72	80	92
R _{TH} , j-l	Thermal Resistance (junction to lead)	°C/W			69.9	
Test Conditions: $V_D = 5 V$ $I_D = 80 \text{ mA Typ.}$ OIP_3 Tone Spacing = 1 MHz, Pout per tone = 0 dBm $T_L = 25^{\circ}C$ $Z_S = Z_L = 50 \text{ Ohms}$ Tested with Bias Tees						

The information provided herein is believed to be reliable at press time. Sirenza Microdevices assumes no responsibility for inaccuracies or omissions. Sirenza Microdevices assumes no responsibility for the use of this information, and all such information shall be entirely at the user's own risk. Prices and specifications are subject to change without notice. No patent rights or licenses to any of the circuits described herein are implied or granted to any third party. Sirenza Microdevices does not authorize or warrant any Sirenza Microdevices product for use in life-support devices and/or systems. Copyright 2001 Sirenza Microdevices, Inc.. All worldwide rights reserved

303 S. Technology Ct. Broomfield, CO 80021

http://www.sirenza.com EDS-103832 Rev D



Typical RF Performance at Key Operating Frequencies (With .5-3.5 GHz Application Circuit)

		Frequency (MHz)						
Symbol	Parameter	Unit	500	850	1950	2500	3500	4000
S ₂₁	Small Signal Gain	dB	15.6	15.6	15.5	15.5	15.5	15.0
OIP ₃	Output Third Order Intercept Point	dBm	38.8	39.3	35.2	32.8	29.1	26.1
P _{1dB}	Output Power at 1dB Compression	dBm	19.2	19.1	19.2	18.6	16.7	14.1
S ₁₁	Input Return Loss	dB	25.1	29.9	19.4	17.6	14.9	21.3
S ₂₂	Output Return Loss	dB	32.1	26.4	17.2	14.7	13.2	17.4
S ₁₂	Reverse Isolation	dB	18.4	18.4	18.9	19.1	19.8	20.8
NF	Noise Figure	dB	4.3	4.3	4.6	4.5	4.8	5.1
Test Condi	Test Conditions:VCC = 5V I_D = 80mA Typ.OIP3 Tone Spacing = 1MHz, Pout per tone = 0 dBm T_L = 25°C Z_S = Z_L = 50 Ohms							







303 S. Technology Ct. Broomfield, CO 80021











303 S. Technology Ct. Broomfield, CO 80021









Broomfield, CO 80021

Phone: (800) SMI-MMIC



Application Schematic



Evaluation Board Layout



Mounting Instructions

- 1. Solder the copper pad on the backside of the device package to the ground plane.
- 2. Use a large ground pad area with many plated through-holes as shown.
- 3. We recommend 1 or 2 ounce copper. Measurement for this datasheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

Application Circuit Element Values

Reference Designator	Frequency (MHz) 500 to 3500
C _B	68pF
L _C	82nH 1008CS

Absolute Maximum Ratings

Parameter	Absolute Limit		
Ma. Dvice Current (I _D)	100 mA		
Max Device Voltage (V _D)	5.5 V		
Max. RF Input Power	+12 dBm		
Max. Operating Dissipated Power	0.55 W		
Max. Junction Temp. (T_J)	+150°C		
Operating Temp. Range (T_L)	-40°C to +85°C		
Max. Storage Temp.	+150°C		
Operation of this device beyond any one of these limits may cause			

permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression: $I_DV_D < (T_J - T_L) / R_{TH}, j$ -l $T_L=T_{LEAD}$



ESD Class 1C

Appropriate precautions in handling, packaging and testing devices must be observed.

MSL (Moisture Sensitivity Level) Rating: Level 1



Suggested PCB Pad Layout



Nominal Package Dimensions

Dimensions in inches (millimeters) Refer to package drawing posted at www.sirenza.com for tolerances

Bottom View



Pin #	Function	Description		
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.		
2, 4	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible		
3	RF OUT/ BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.		

Part Number Ordering Information

Part Number	Reel Size	Devices / Reel
SBB-4089	7"	1000
SBB-4089Z	7"	1000

303 S. Technology Ct. Broomfield, CO 80021

4

BB4Z

2

Lead Free

1

3